

- Drafts
- Pending
- Active
 - L9: (119920) memory adj cell
 - L10: (14179) first adj2 page
 - L11: (7963) second adj2 page
 - L12: (186930) reference adj2 (voltage or potential)
 - L13: (145) 9 same 10
 - L14: (11) 12 same 13
 - L18: (81) 11 same 13
 - L19: (70) 18 not 14
 - L20: (42) read\$4 same 19
 - L27: (11658) 365/185\$3
 - L28: (0) 27 and 1 and 2
 - L29: (187) 27 and 9 and 10
 - L30: (100) 29 not 13
 - L31: (179) (KATO near2 YOSHIHARU).in.
- Failed
- Saved
- Favorites
- Tagged (4)
- UDC
- Queue
- Trash

Search
List
Browse
Queue
Clear

DBs
USPAT; US-PGPUB; EPO; JPO; DERVENT; IBM_TDB
 Plurals

Default operator: OR
 Highlight all hit terms initially

U	1	2	Document ID	Issue Date	Inventor	Current OR	Current XRe	Retrieval C	Title	Page	S	C	P
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20030169630 A1	20030911	Hosono, Koji et al.	365/200			Non-volatile semiconductor memory device	33	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 5625590 A	19970429	Choi, Beyng-Sun et al.	365/185.17	365/185.11;		Nonvolatile semiconductor memory	27	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6288936 B1	20010911	Kawamura, Shoichi	365/185.03	365/185.05;		Nonvolatile memory for storing multivalue data	27	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6600676 B2	20030729	Shibata, Noboru et al.	365/185.04	365/185.24;	365/185.03;	Nonvolatile semiconductor memory device with a ROM	59	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>